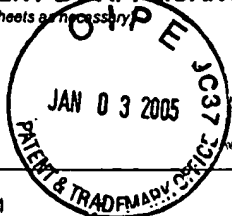


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Complete if Known

Application Number	10/634,274
Filing Date	August 5, 2003
First Named Inventor	Farrar, Paul
Group Art Unit	2823
Examiner Name	Kebede, Brook

Sheet 1 of 1

Attorney Docket No: 1303.110US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
Bu	US-6,350,678	02/26/2002	Pramanick, S., et al.	03/23/2000
Bu	US-6,376,368	04/23/2002	Jung, S., et al.	08/01/2000

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Brook Kebede

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3/14/2005

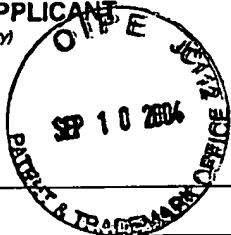
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STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/634,274
Filing Date	August 5, 2003
First Named Inventor	Farrar, Paul
Group Art Unit	2823
Examiner Name	Kebede, Brook

Sheet 1 of 1

Attorney Docket No: 1303.110US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
BN	US-6,208,016	03/27/2001	Farrar, Paul	257	643	02/24/1999
BN	US-6,288,442	09/11/2001	Farrar, Paul A.	257	678	09/10/1998
BN	US-6,358,849	03/19/2002	Havemann, R. H., et al.	438	689	12/21/1999
BN	US-6,552,432	04/22/2003	Farrar, Paul A.	257	751	08/30/2001
BN	US-6,614,099	09/02/2003	Farrar, Paul A.	257	643	09/04/2001
BN	US-6,743,716	06/01/2004	Farrar, Paul A.	438	652	07/16/2002
BN	US-6,756,298	06/29/2004	Ahn, Kie Y., et al.	438	635	08/01/2002

EXAMINER

Brook Kebede

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3/14/2005

Substitute Disclosure Statement Form (PTO-1448)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached

	First Named Inventor	Farrar, Paul
	Group Art Unit	2818-2823
	Examiner Name	Unknown- B. KEBEDE
Sheet 1 of 12		Attorney Docket No: 1303.110US1

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
BU	2001/0002333	05/31/2001	Huang, Chao-Yuan, et al.	438	637	03/29/1999
BU	2002/0014646	02/07/2002	Tsu, Robert, et al.	257	296	07/30/2001
BU	2002/0028552	03/07/2002	Lee, Ki-Young, et al.	438	243	09/03/1999
BU	2002/0096768	07/25/2002	Joshi, Rajiv V.	257	750	01/18/2002
BU	2002/0109233	08/15/2002	Farrar, Paul A.	257	762	04/05/2002
BU	US-2,842,438	07/08/1958	Saarivirta, M. J., et al.	75	153	08/02/1956
BU	US-3,954,570	06/04/1976	Shirk, Albert, et al.	204	15	11/11/1974
BU	US-4,386,116	05/31/1983	Nair, Krishna K., et al.	427	99	12/24/1981
BU	US-4,394,223	07/19/1983	Hall, Dean	204	15	10/06/1981
BU	US-4,423,547	01/03/1984	Farrar, P. A., et al.	29	571	06/01/1981
BU	US-4,565,157	01/21/1986	Brors, D. L., et al.	118	719	03/29/1983
BU	US-4,574,095	03/04/1986	Baum, Thomas H., et al.	427	53.1	11/19/1984
BU	US-4,762,728	08/09/1988	Keyser, T., et al.	427	38	11/26/1985
BU	US-4,788,082	11/29/1988	Schmitt, Jerome J.	427	248.1	12/12/1985
BU	US-4,847,111	07/11/1989	Chow, Yu C., et al.	427	38	06/30/1988
BU	US-4,931,410	06/05/1990	Tokunaga, Takafumi, et al.	437	189	08/25/1988
BU	US-4,948,459	08/14/1990	Van Laarhoven, et al.	156	643	01/04/1989
BU	US-4,962,058	10/09/1990	Cronin, John E., et al.	437	187	04/14/1989
BU	US-4,996,584	02/26/1991	Young, P. L., et al.	357	71	10/13/1988
BU	US-5,019,531	05/28/1991	Awaya, N., et al.	437	180	05/19/1989
BU	US-5,034,799	07/23/1991	Tomita, K., et al.	357	71	02/14/1990
BU	US-5,084,412	01/28/1992	Nakasaka, Yasushi	437	189	10/01/1990
BU	US-5,100,499	03/31/1992	Douglas, M. A.	156	635	06/25/1991
BU	US-5,130,274	07/14/1992	Harper, J. M., et al.	437	195	04/05/1991
BU	US-5,149,615	09/22/1992	Chakravorty, K. K., et al.	430	313	01/08/1991
BU	US-5,158,986	10/27/1992	Cha, S. W., et al.	521	82	04/05/1991
BU	US-5,173,442	12/22/1992	Carey, D. H.	437	173	03/24/1992
BU	US-5,231,056	07/27/1993	Sandhu, G. S.	437	200	01/15/1992
BU	US-5,240,878	08/31/1993	Fitzsimmons, J., et al.	437	187	04/26/1991
BU	US-5,243,222	09/07/1993	Harper, J. M., et al.	257	774	01/08/1992
BU	US-5,256,205	10/26/1993	Schmitt III, Jerome J., et al.	118	723	01/07/1992
BU	US-5,334,356	08/02/1994	Baldwin, D. F., et al.	422	133	08/24/1992
BU	US-5,354,712	10/11/1994	Ho, Y. Q., et al.	437	195	11/12/1992

EXAMINER

B. KEBEDE

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Substitute Disclosure Statement Form (PTO-1449)
 * EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

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Application Number	10/634274
Filing Date	August 5, 2003
First Named Inventor	Farrar, Paul
Group Art Unit	2818 2823
Examiner Name	Unknown B. KEBEDE

Sheet 2 of 12

Attorney Docket No: 1303.110US1

BU	US-5,371,042	12/06/1994	Ong, E.	437	194	06/16/1992
BU	US-5,384,284	01/24/1995	Doan, T T., et al.	437	190	10/01/1993
BU	US-5,413,687	05/09/1995	Barton, C. L., et al.	204	192.14	11/27/1991
BU	US-5,426,330	06/20/1995	Joshi, R. V., et al.	257	752	09/21/1993
BU	US-5,442,237	08/15/1995	Hughes, Henry G., et al.	257	759	02/04/1994
BU	US-5,447,887	09/05/1995	Filipiak, Stanley, et al.	437	200	04/01/1994
BU	US-5,461,243	10/24/1995	Ek, Bruce A., et al.	257	190	10/29/1993
BU	US-5,470,789	11/28/1995	Misawa, N.	437	190	03/07/1995
BU	US-5,470,801	11/28/1995	Kapoor, Ashok K., et al.	437	238	06/28/1993
BU	US-5,476,817	12/19/1995	Numata, K.	437	195	05/31/1994
BU	US-5,495,667	03/05/1996	Farnworth, Warren M., et al.	29	843	11/07/1994
BU	US-5,506,449	04/09/1996	Nakano, Tadashi, et al.	257	758	03/23/1994
BU	US-5,529,956	06/25/1996	Morishita, Y.	437	195	09/28/1994
BU	US-5,538,922	07/23/1996	Cooper, K J., et al.	437	195	01/25/1995
BU	US-5,539,060	07/23/1996	Tsunogae, Y., et al.	525	338	10/13/1995
BU	US-5,595,937	01/21/1997	Mikagi, K.	437	192	04/12/1996
BU	US-5,609,721	03/11/1997	Tsukune, A., et al.	156	646.1	01/03/1995
BU	US-5,625,232	04/29/1997	Numata, K., et al.	257	758	07/15/1994
BU	US-5,635,253	06/03/1997	Canaperi, Donald F., et al.	427	437	06/07/1995
BU	US-5,654,245	08/05/1997	Allen, Gregory L.	438	629	03/23/1993
BU	US-5,662,788	09/02/1997	Sandhu, G., et al.	205	87	06/03/1996
BU	US-5,670,420	09/23/1997	Choi, Kyeong K.	437	189	11/08/1995
BU	US-5,674,787	10/07/1997	Zhao, Bin, et al.	437	230	01/16/1996
BU	US-5,675,187	10/07/1997	Numata, K., et al.	257	758	05/16/1996
BU	US-5,679,608	10/21/1997	Cheung, Robin W., et al.	437	195	06/05/1995
BU	US-5,681,441	10/28/1997	Svendsen, Leo G., et al.	205	114	12/22/1992
BU	US-5,695,810	12/09/1997	Dubin, Valery M., et al.	427	96	11/20/1996
BU	US-5,719,089	02/17/1998	Cherng, Meng-Jaw, et al.	438	637	06/21/1996
BU	US-5,719,410	02/17/1998	Suehiro, Shintaro, et al.	257	77	12/16/1996
BU	US-5,739,579	04/14/1998	Chiang, Chien, et al.	257	635	09/10/1996
BU	US-5,763,953	06/09/1998	Iijima, T., et al.	257	762	01/18/1996
BU	US-5,780,358	07/14/1998	Zhou, M. S.	438	645	04/08/1996
BU	US-5,785,570	07/28/1998	Bruni, M. D.	445	52	07/25/1995

EXAMINER

Bruni KEBEDE

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/634274
Filing Date	August 5, 2003
First Named Inventor	Farrar, Paul
Group Art Unit	2818 2823
Examiner Name	Unknown B. KEBEDU

Sheet 3 of 12

Attorney Docket No: 1303.110US1

BU	US-5,792,522	08/11/1998	Jin, S., et al.	427	575	09/18/1996
BU	US-5,801,098	09/01/1998	Fiordalice, R., et al.	438	653	09/03/1996
BU	US-5,814,557	09/29/1998	Venkatraman, Ramnath, et al.	438	622	05/20/1996
BU	US-5,821,168	10/13/1998	Jain, Ajay	438	692	07/16/1997
BU	US-5,824,599	10/20/1998	Schacham-Diamond, Yosef, et al.	438	678	01/16/1996
BU	US-5,858,877	01/12/1999	Dennison, C. H., et al.	438	700	01/21/1997
BU	US-5,891,797	04/06/1999	Farrar, P. A.	438	619	10/20/1997
BU	US-5,891,804	04/06/1999	Havemann, R. H., et al.	438	674	04/14/1997
BU	US-5,893,752	04/13/1999	Zhang, J., et al.	438	687	12/22/1997
BU	US-5,895,740	04/20/1999	Chien, Rong-Wu, et al.	430	313	11/13/1996
BU	US-5,897,370	04/27/1999	Joshi, R. V., et al.	438	632	10/28/1996
BU	US-5,907,772	05/25/1999	Iwasaki, Haruo	438	253	02/26/1997
BU	US-5,911,113	06/08/1999	Yao, G., et al.	438	649	03/18/1997
BU	US-5,913,147	06/15/1999	Dubin, Valery, et al.	438	687	01/21/1997
BU	US-5,925,930	07/20/1999	Farnworth, Warren M., et al.	257	737	05/21/1996
BU	US-5,930,669	07/27/1999	Uzoh, Cyprian	438	627	04/03/1997
BU	US-5,932,928	08/03/1999	Clampitt, D. A.	257	758	07/03/1997
BU	US-5,933,758	08/03/1999	Jain, A.	438	687	05/12/1997
BU	US-5,940,733	08/17/1999	Beinglass, Israel, et al.	438	655	07/29/1997
BU	US-5,948,467	09/07/1999	Nguyen, T., et al.	427	99	07/24/1998
BU	US-5,962,923	10/05/1999	Xu, Z., et al.	257	774	08/07/1995
BU	US-5,968,333	10/19/1999	Nogami, T., et al.	205	184	04/07/1998
BU	US-5,969,422	10/19/1999	Ting, C., et al.	257	762	05/15/1997
BU	US-5,972,179	10/26/1999	Chittipeddi, et al.	204	192.17	09/30/1997
BU	US-5,972,804	10/26/1999	Tobin, Philip J., et al.	438	786	11/03/1997
BU	US-5,976,710	11/02/1999	Sachdev, K. G., et al.	428	620	04/10/1997
BU	US-5,981,350	11/09/1999	Geusic, Joseph E., et al.	438	386	05/29/1998
BU	US-5,985,759	11/16/1999	Kim, E., et al.	438	653	02/24/1998
BU	US-5,989,623	11/23/1999	Chen, Liang-Yuh, et al.	427	97	08/19/1997
BU	US-5,994,777	11/30/1999	Farrar, P. A.	257	758	08/26/1998
BU	US-6,001,730	12/14/1999	Farkas, J., et al.	438	627	10/20/1997
BU	US-6,008,117	12/28/1999	Hong, Qi-Zhong, et al.	438	629	03/19/1997
BU	US-6,015,465	01/18/2000	Kholodenko, A., et al.	118	719	04/08/1998
BU	US-6,017,820	01/25/2000	Ting, C. H., et al.	438	689	07/17/1998

EXAMINER

B. KEBEDU

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Substitute Disclosure Statement Form (PTO-1449)

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Application Number 10/634274

Filing Date August 5, 2003

First Named Inventor Farrar, Paul

Group Art Unit 2818 J823

Examiner Name Unknown B. KEBEDE

Sheet 4 of 12

Attorney Docket No: 1303.110US1

BU	US-6,030,877	02/29/2000	Lee, C , et al.	438	381	10/06/1997
BU	US-6,037,248	03/14/2000	Ahn, Kie	438	619	06/13/1997
BU	US-6,054,172	04/25/2000	Robinson, K. , et al.	427	97	02/25/1999
BU	US-6,065,424	05/23/2000	Shacham-Diamond, Y. , et al.	118	696	12/18/1996
BU	US-6,069,068	05/30/2000	Rathore, H. S. , et al.	438	628	10/08/1997
BU	US-6,071,810	06/06/2000	Wada, Junichi , et al.	438	635	12/23/1997
BU	US-6,077,792	06/20/2000	Farrar, Paul A.	438	780	07/14/1997
BU	US-6,100,193	08/08/2000	Suehiro, Shintaro, et al.	438	685	09/24/1997
BU	US-6,120,641	10/19/2000	Stevens, E. Henry , et al.	156	345.22	08/03/1998
BU	US-6,126,989	10/03/2000	Robinson, Karl , et al.	427	97	08/26/1998
BU	US-6,136,095	10/24/2000	Xu, Z. , et al.	118	719	10/06/1997
BU	US-6,139,699	10/31/2000	Chiang, T. , et al.	204	192.15	05/27/1997
BU	US-6,140,228	10/31/2000	Shan, E. , et al.	438	653	11/13/1997
BU	US-6,140,234	10/31/2000	Uzoh, Cyprian , et al.	438	678	01/20/1998
BU	US-6,143,646	11/07/2000	Wetzel, J. T.	438	637	06/03/1997
BU	US-6,150,261	11/21/2000	Hsu, C. , et al.	438	640	05/25/1999
BU	US-6,153,507	11/28/2000	Mikagi, K.	438	618	01/13/1998
BU	US-6,159,769	12/12/2000	Farnworth, Warren M., et al.	438	108	01/05/1999
BU	US-6,168,704	01/02/2001	Brown, T. M., et al.	205	118	02/04/1999
BU	US-6,171,661	01/09/2001	Zheng, B. , et al.	427	535	02/25/1998
BU	US-6,177,350	01/23/2001	Sundarajan, A., et al.	438	688	04/14/1998
BU	US-6,183,564	02/06/2001	Reynolds, G. J., et al.	118	719	11/12/1998
BU	US-6,187,656	02/01/2001	Lu, Jiong P., et al.	438	592	10/07/1998
BU	US-6,190,732	02/20/2001	Omstead, , et al.	118	729	
BU	US-6,197,688	03/06/2001	Simpson, Cindy R.	438	678	02/12/1998
BU	US-6,207,222	03/27/2001	Chen, Liang-Yuh , et al.	427	97	08/24/1999
BU	US-6,207,553	05/27/2001	Buynoski, M. , et al.	438	622	01/26/1999
BU	US-6,207,558	03/27/2001	Singhvi, Shri , et al.	438	648	10/01/1999
BU	US-6,211,049	04/03/2001	Farrar, Paul A.	438	597	02/24/1999
BU	US-6,211,073	04/03/2001	Ahn, K. Y.	438	653	02/27/1998
BU	US-6,221,763	04/24/2001	Gilton, Terry L.	438	643	04/05/1999
BU	US-6,232,219	05/15/2001	Blalock, , et al.	438	637	05/20/1998
BU	US-6,249,056	06/19/2001	Kwon, Dong-chul, et al.	257	758	11/01/1999
BU	US-6,265,311	07/24/2001	Hautala, J J., et al.	438	680	04/27/1999
BU	US-6,271,592	08/07/2001	Kim, E. , et al.	257	751	08/06/1999
BU	US-6,277,263	08/21/2001	Chen, Linlin	205	182	08/31/1999
BU	US-6,284,656	09/04/2001	Farrar, Paul A.	438	687	08/04/1998

EXAMINER

Brook Kebede

DATE CONSIDERED

3/14/2005

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/634274
Filing Date	August 5, 2003
First Named Inventor	Farrar, Paul
Group Art Unit	2818 2823
Examiner Name	Unknown B. KEBEDE

Sheet 5 of 12

Attorney Docket No: 1303.110US1

BU	US-6,287,954	09/11/2001	Ashley, Leon, et al.	438	622	12/09/1999
BU	US-6,290,833	09/18/2001	Chen, Linlin	205	182	08/31/1999
BU	US-6,313,035	11/06/2001	Sandhu, Gurtej S., et al.	438	681	05/31/1996
BU	US-6,323,553	11/01/2001	Hsu, Wei-Yung, et al.	257	751	11/01/2001
BU	US-6,326,303	12/04/2001	Robinson, Karl, et al.	438	678	02/11/2000
BU	US-6,342,448	01/29/2002	Lin, J., et al.	438	687	05/31/2000
BU	US-6,358,842	03/19/2002	Zhou, Mei-Sheng, et al.	438	633	08/07/2000
BU	US-6,359,328	03/01/2002	Dubin,	257	622	
BU	US-6,368,966	04/09/2002	Krishnamoorthy, Ahila, et al.	438	687	08/31/1999
BU	US-6,372,622	04/16/2002	Tan, et al.	438	612	10/26/1999
BU	US-6,376,370	04/23/2002	Farrar, Paul A.	438	678	01/18/2000
BU	US-6,383,920	05/07/2002	Wang, P., et al.	438	639	01/10/2001
BU	US-6,387,542	05/14/2002	Kozlov, Alexander, et al.	428	673	07/06/2000
BU	US-6,399,489	06/04/2002	M'Saad, H., et al.	438	680	11/01/1999
BU	US-6,403,481	06/11/2002	Matsuda, T., et al.	438	687	08/10/1999
BU	US-6,420,262	07/16/2002	Farrar, Paul A.	438	652	01/18/2000
BU	US-6,426,289	07/30/2002	Farrar, Paul A.	438	670	03/24/2000
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Application Number	10/634274
Filing Date	August 5, 2003
First Named Inventor	Farrar, Paul
Group Art Unit	2818 2823
Examiner Name	Unknown B. KEBEDE

Attorney Docket No: 1303.110US1

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Complete if Known

Application Number	10/634274
Filing Date	August 5, 2003
First Named Inventor	Farrar, Paul
Group Art Unit	2818-2823
Examiner Name	Unknown B. KEBEDE

Sheet 12 of 12

Attorney Docket No: 1303.110US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.†	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T‡
BK	1	ZHANG, J., et al., "Investigations of photo-induced decomposition of palladium acetate for electroless copper plating", Thin Solid Films, 318, (1998), pp. 234-238	

EXAMINER

Brown Kebede

DATE CONSIDERED

3/04/2005

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